

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
 SPRINGFIELD, NEW JERSEY 07081
 U.S.A.

TELEPHONE: (973) 376-2922
 (212) 227-6005
 FAX: (973) 376-8960

GENERAL DESCRIPTION

The MPA-201 is an amplifier device designed for broadband performance to 500 MHz in a format suitable for stripline assembly and high reliability applications. Its wide dynamic range and flexibility commend it for a broad spectrum of instrumentation, receiver and transmitter applications.

FEATURES

- Useable for broadband or narrowband applications
- Useable DC to 500 MHz
- Uniform gain with frequency
- Internally matched to 50 ohms
- Cascadable
- Gold Metallization

WIDE DYNAMIC RANGE

- Low Distortion - 3rd order intercept point +40dBm typical at 230 MHz
- Low Noise Figure - 6.0 dB typical at 200 MHz

HIGH OUTPUT POWER

1dB Compression Power

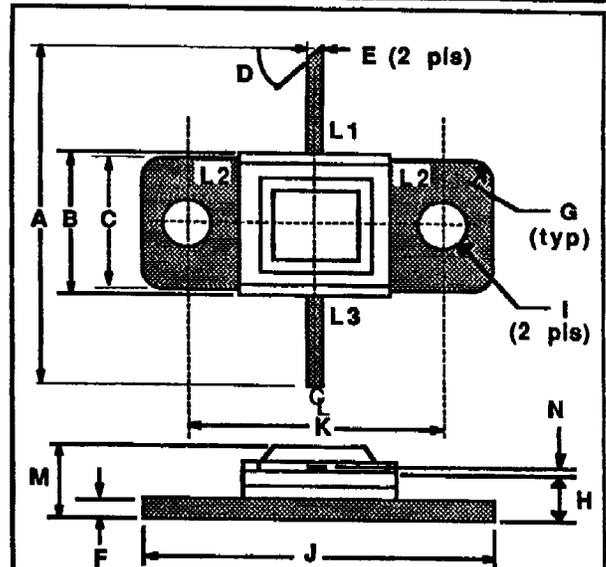
800 mW minimum	30 MHz (+29 dBm)
800 mW typical	70 MHz (+29 dBm)
400 mW minimum	400 MHz (+29 dBm)
315 mW minimum	500 MHz (+25 dBm)

Maximum Temperatures

Storage temperature	-55 to +200 °C
Operating Flange Temperature	-55 to +125 °C

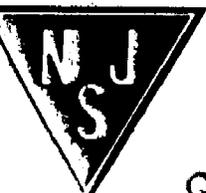
MPA 201
0.5 WATTS - 12.5 VOLTS
500 MHz

50Ω HYBRID AMPLIFIER



DIM	Millimeter	TOL	Inches	TOL
A	20.32	.76	.800	.030
B	10.16	.13	.400	.005
C	9.78	.13	.385	.005
D	45°	5°	45°	5°
E	1.27	.13	.050	.005
F	1.52	.13		.005
G	1.52 R	.13	.060 R	.005
H	3.05	.13	.120	.005
I	3.30 DIA	.13	.130 DIA	.005
J	22.86	.13	.900	.005
K	16.51	.13	.650	.005
M	4.70	REF	.185	REF
N	0.13	.02	.005	.001

L1 : RF Output
 L2 : Ground
 L3 : RF Input



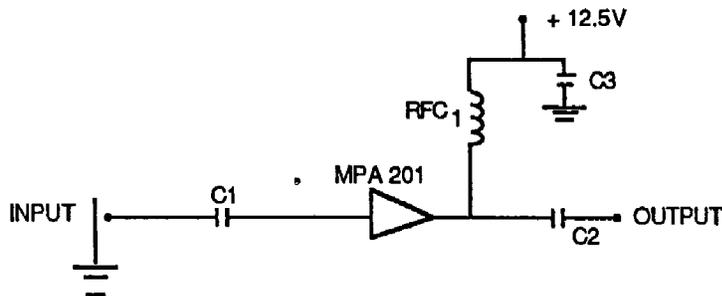
NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

ELECTRICAL CHARACTERISTICS¹

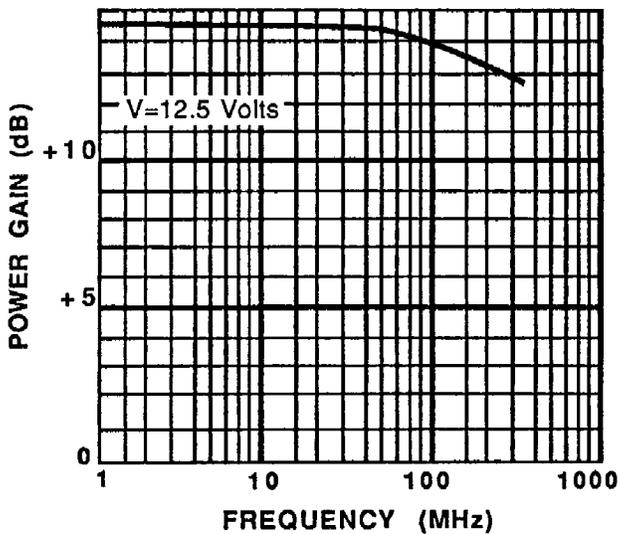
SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
P _{out}	Power Output	f = 1-500 MHz V _{dc} = 12.5V		500		mW
P _{in}	Power Input				+13	dBm
VSWR	Input VSWR			1.5:1	2.0:1	
G _a	Small Signal Gain		12	13		dB
ΔG _a	Gain Flatness			±0.6	±1.0	dB
P _{1dB}	Power Out @ 1dB Gain Compression		+25	+27		dBm
I _{dc}	DC Current			250		mA
Δt _{jf}	Temperature Rise Junction to Flange				+50	°C
I _p	3rd Order Intercept Point		+37	+40	dBm	
N _f	Noise Figure	f = 200 MHz V _{dc} = 12.5V		6.0		dB

Note 1: T_c = +25°C unless otherwise specified



RFC₁ = 4.7 μh
C1, C2 = .01 μf chip
C3 = 0.1 μf

POWER GAIN VS FREQUENCY (TYPICAL)



1dB COMPRESSION POINT VS FREQUENCY (TYPICAL)

